



PTO/SB/08a/b (08-03)

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Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Complete if Known	
				Application Number	10/769,787-Conf. #9244
				Filing Date	February 3, 2004
				First Named Inventor	John T. Moore
				Art Unit	2812-2822
				Examiner Name	Not Yet Assigned T.M. Thomas
Sheet	1	of	3	Attorney Docket Number	M4065.0989/P989-A

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
JMS	A	US 2004/0035401	2/2004	Ramachandran et al.	
	B	US 2003/0212724	11/2003	Ovshinsky et al.	
	C	US 2003/0048744	3/2003	Ovshinsky et al.	
	D	US 2003/0212725	11/2003	Ovshinsky et al.	
	E	US RE 37,259E	7/2001	Ovshinsky	
	F	US 3,271,591	9/1966	Ovshinsky	
	G	US 3,961,314	6/1976	Klose et al.	
	H	US 3,966,317	6/1976	Wacks et al.	
	I	US 3,983,542	11/1976	Ovshinsky	
	J	US 3,988,720	10/1976	Ovshinsky	
	K	US 4,177,474	12/1979	Ovshinsky	
	L	US 4,267,261	5/1981	Hallman et al.	
	M	US 4,597,162	7/1986	Johnson et al.	
	N	US 4,608,296	8/1986	Keem et al.	
	O	US 4,637,895	1/1987	Ovshinsky et al.	
	P	US 4,646,266	2/1987	Ovshinsky et al.	
	Q	US 4,664,939	5/1987	Ovshinsky	
	R	US 4,668,968	5/1987	Ovshinsky et al.	
	S	US 4,670,763	6/1987	Ovshinsky et al.	
	T	US 4,673,957	6/1987	Ovshinsky et al.	
	U	US 4,678,679	7/1987	Ovshinsky	
	V	US 4,696,758	9/1987	Ovshinsky et al.	
	W	US 4,698,234	10/1987	Ovshinsky et al.	
	X	US 4,710,899	12/1987	Young et al.	
	Y	US 4,728,406	3/1988	Banerjee et al.	
	Z	US 4,737,379	4/1988	Hudgens et al.	
	A1	US 4,766,471	8/1988	Ovshinsky et al.	
	B1	US 4,769,338	9/1988	Ovshinsky et al.	
	C1	US 4,775,425	10/1988	Guha et al.	
	D1	US 4,788,594	11/1988	Ovshinsky et al.	
	E1	US 4,809,044	2/1989	Pryor et al.	
	F1	US 4,818,717	4/1989	Johnson et al.	
	G1	US 4,843,443	6/1989	Ovshinsky et al.	
	H1	US 4,845,533	7/1989	Pryor et al.	
	I1	US 4,853,785	8/1989	Ovshinsky et al.	
	J1	US 4,891,330	1/1990	Guha et al.	
	K1	US 5,128,099	7/1992	Strand et al.	
	L1	US 5,159,661	10/1992	Ovshinsky et al.	
	M1	US 5,166,758	11/1992	Ovshinsky et al.	
	N1	US 5,177,567	1/1993	Klersy et al.	
JMS	O1	US 5,296,716	3/1994	Ovshinsky et al.	

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JMJ	P1	US 5,335,219	8/1994	Ovshinsky et al.	
	Q1	US 5,359,205	10/1994	Ovshinsky	
	R1	US 5,341,328	8/1994	Ovshinsky et al.	
	S1	US 5,406,509	4/1995	Ovshinsky et al.	
	T1	US 5,414,271	5/1995	Ovshinsky et al.	
	U1	US 5,534,711	7/1996	Ovshinsky et al.	
	V1	US 5,534,712	7/1996	Ovshinsky et al.	
	W1	US 5,536,947	7/1996	Klersy et al.	
	X1	US 5,543,737	8/1996	Ovshinsky	
	Y1	US 5,591,501	1/1997	Ovshinsky et al.	
	Z1	US 5,596,522	1/1997	Ovshinsky et al.	
	A2	US 5,687,112	11/1997	Ovshinsky	
	B2	US 5,694,054	12/1997	Ovshinsky et al.	
	C2	US 5,714,768	2/1998	Ovshinsky et al.	
	D2	US 5,825,046	10/1998	Czubatyj et al.	
	E2	US 5,912,839	6/1999	Ovshinsky et al.	
	F2	US 5,933,365	8/1999	Klersy et al.	
	G2	US 6,011,757	1/2000	Ovshinsky	
	H2	US 6,087,674	7/2000	Ovshinsky et al.	
	I2	US 6,141,241	10/2000	Ovshinsky et al.	
	J2	US 6,339,544	1/2002	Chiang et al.	
	K2	US 6,404,665	6/2002	Lowery et al.	
	L2	US 6,429,064	8/2002	Wicker	
	M2	US 6,437,383	8/2002	Xu	
	N2	US 6,462,984	10/2002	Xu et al.	
	O2	US 6,480,438	11/2002	Park	
	P2	US 6,487,113	11/2002	Park et al.	
	Q2	US 6,501,111	12/2002	Lowery	
	R2	US 6,507,061	1/2003	Hudgens et al.	
	S2	US 6,511,862	1/2003	Hudgens et al.	
	T2	US 6,511,867	1/2003	Lowery et al.	
	U2	US 6,512,241	1/2003	Lai	
	V2	US 6,514,805	2/2003	Xu et al.	
	W2	US 6,531,373	3/2003	Gill et al.	
	X2	US 6,534,781	3/2003	Dennison	
	Y2	US 6,545,287	4/2003	Chiang	
	Z2	US 6,545,907	4/2003	Lowery et al.	
	A3	US 6,555,860	4/2003	Lowery et al.	
	B3	US 6,563,164	5/2003	Lowery et al.	
	C3	US 6,566,700	5/2003	Xu	
	D3	US 6,567,293	5/2003	Lowery et al.	
	E3	US 6,569,705	5/2003	Chiang et al.	
	F3	US 6,570,784	5/2003	Lowery	
	G3	US 6,576,921	6/2003	Lowery	
JMJ	H3	US 6,586,761	7/2003	Lowery	

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				Art Unit	2812 2822
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JM3	I3	US 6,589,714	7/2003	Maimon et al.	
	J3	US 6,590,807	7/2003	Lowery	
	K3	US 6,593,176	7/2003	Dennison	
	L3	US 6,597,009	7/2003	Wicker	
	M3	US 6,605,527	8/2003	Dennison et al.	
	N3	US 6,613,604	9/2003	Maimon et al.	
	O3	US 6,621,095	9/2003	Chiang et al.	
	P3	US 6,625,054	9/2003	Lowery et al.	
	Q3	US 6,642,102	11/2003	Xu	
	R3	US 6,646,297	11/2003	Dennison	
	S3	US 6,649,928	11/2003	Dennison	
	T3	US 6,667,900	12/2003	Lowery et al.	
	U3	US 6,671,710	12/2003	Ovshinsky et al.	
	V3	US 6,673,648	1/2004	Lowrey	
	W3	US 6,673,700	1/2004	Dennison et al.	
	X3	US 6,674,115	1/2004	Hudgens et al.	
	Y3	US 6,687,427	2/2004	Ramalingam et al.	
	Z3	US 6,690,026	2/2004	Peterson	
	A4	US 6,696,355	2/2004	Dennison	
	B4	US 6,687,153	2/2004	Lowery	
	C4	US 6,707,712	3/2004	Lowery	
JM3	D4	US 6,714,954	3/2004	Ovshinsky et al.	

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Examiner Initials*	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³	Number ⁴ Kind Code ⁵ (if known)				

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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²

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				Application Number	NOT YET ASSIGNED
				Filing Date	Concurrently Herewith
				First Named Inventor	John T. Moore, et al.
				Art Unit	N/A 2822
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U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
JMT	AB**	2002/0072188	6/13/2002	Gilton	
	AC**	2002/0106849	08/08/2002	Moore	
	AH**	2002/0123169	09/05/2002	Moore et al.	
	AI**	2002/0123170	09/05/2002	Moore et al.	
	AJ**	2002/0123248	09/05/2002	Moore et al.	
	AK**	2002/0127886	09/12/2002	Moore et al.	
	AL**	2002/0132417	09/09/2002	Li	
	**	2002/0160551	10/31/2002	Harshfield	
	AF**	2002/0163828	11/07/2002	Krieger et al.	
	AM**	2002/0168852	11/14/2002	Harshfield et al.	
	AN**	2002/0190289	12/19/2002	Harshfield et al.	
	AP**	2003/0001229	01/02/2003	Moore et al.	
	AQ**	2003/0027416	02/06/2003	Moore	
	AR**	2003/0032254	02/13/2003	Gilton	
	AU**	2003/0038301	02/27/2003	Moore	
	AV**	2003/0043631	03/06/2003	Gilton et al.	
	AW**	2003/0045049	03/06/2003	Campbell et al.	
	AX**	2003/0045054	03/06/2003	Campbell et al.	
	AY**	2003/0047765	03/13/2003	Campbell	
	AZ**	2003/0047772	03/13/2003	Li	
	AA1**	2003/0047773	03/13/2003	Li	
	AC1**	2003/0049912	03/13/2003	Campbell et al.	
	AD1**	2003/0068861	04/10/2003	Li	
	AE1**	2003/0068862	04/10/2003	Li	
	AF1**	2003/0095426	05/22/2003	Hush et al.	
	AG1**	2003/0096497	05/22/2003	Moore et al.	
	AH1**	2003/0107105	06/12/2003	Kozicki	
	AI1**	2003/0117831	06/26/2003	Hush	
	AJ1**	2003/0128612	07/10/2003	Moore et al.	
	AK1**	2003/0137869	07/24/2003	Kozicki	
	AL1**	2003/0143782	07/31/2003	Gilton et al.	
	**	2003/1055589	08/21/2003	Campbell et al.	
	**	2003/0155606	08/21/2003	Campbell et al.	
	AM1**	2003/0156447	08/21/2003	Kozicki	
	AN1**	2003/0156463	08/21/2003	Casper et al.	
	AO1**	3,622,319	11/1971	Sharp	
	AP1**	3,743,847	7/1973	Boland	
	AQ1**	4,269,935	5/1981	Masters et al.	
	AR1**	4,312,938	1/1982	Drexler, et al.	
	AS1**	4,316,946	1/1982	Masters, et al.	
	AT1**	4,320,191	3/1982	Yoshikawa et al.	
	AU1**	4,405,710	9/1983	Balasubramanyam et al.	
	AV1**	4,419,421	12/1983	Wichelhaus, et al.	
JMT	AW1**	4,499,557	2/1985	Holmberg et al.	

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				First Named Inventor	John T. Moore, et al.	
				Art Unit	N/A 2822	
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Sheet	2	of	11			

JMJ	AX1**	4,671,618	06/09/1987	Wu et al.	
	AY1**	4,795,657	1/1989	Formigoni et al.	
	AZ1**	4,800,526	01/24/1989	Lewis	
	AA2**	4,847,674	7/1989	Sliwa et al.	
	AB2**	5,177,567	1/1993	Klersy et al.	
	AC2**	5,219,788	6/1993	Abermathey et al.	
	AD2**	5,238,862	8/1993	Blalock et al.	
	AE2**	5,272,359	12/21/1993	Nagasubramanian et al.	
	AF2**	5,314,772	5/24/1994	Kozicki	
	AG2**	5,315,131	5/1994	Kishimoto et al.	
	AH2**	5,350,484	9/1994	Gardner et al.	
	AI2**	5,360,981	11/1994	Owen et al.	
	AJ2**	5,500,532	3/19/1996	Kozicki et al.	
	AK2**	5,512,328	4/1996	Yoshimura et al.	
	AL2**	5,512,773	4/1996	Wolf et al.	
	AM2**	5,726,083	3/1998	Takaishi	
	AN2**	5,751,012	5/12/1998	Wolstenholme et al.	
	AP2**	5,789,277	8/1998	Zahorik et al.	
	**	5,814,527	9/29/1998	Wolstenholme et al.	
	**	5,818,749	10/06/1998	Harshfield	
	AQ2**	5,841,150	11/1998	Gonzalez et al.	
	AR2**	5,846,889	12/1998	Harbison et al.	
	**	5,851,882	12/22/1998	Harshfield	
	**	5,869,843	2/9/1999	Harshfield	
	AU2**	5,920,788	7/1999	Reinberg	
	AV2**	5,998,066	12/1999	Block et al.	
	**	6,031,287	2/29/2000	Harshfield	
	AW2**	6,072,716	06/06/2000	Jacobson et al.	
	AX2**	6,077,729	6/2000	Harshfield	
	AZ2**	6,177,338	1/2001	Liaw et al.	
	AA3**	6,117,720	9/2000	Harshfield	
	AB3**	6,143,604	11/2000	Chiang et al.	
	AC3**	6,236,059	5/2001	Wolsteinholme et al.	
	AD3**	6,297,170	10/2001	Gabriel et al.	
	AE3**	6,300,684	10/2001	Gonzalez et al.	
	AF3**	6,316,784	11/2001	Zahorik et al.	
	AG3**	6,329,606	12/2001	Freyman et al.	
	AH3**	6,348,365	2/19/2002	Moore et al.	
	AI3**	6,350,679	2/2002	McDaniel et al.	
	AJ3**	6,376,284	4/2002	Gonzalez et al.	
	AL3**	6,391,688	5/2002	Gonzalez et al.	
	AM3**	6,414,376	7/2002	Thakur et al.	
	**	6,420,725	7/16/2002	Harshfield	
	AQ3**	6,423,628	7/2002	Li et al.	
	**	6,440,837	8/27/2002	Harshfield	
	AQ3**	6,473,332	10/2002	Ignatiev et al.	
	**	5,761,115	06/02/98	Kozicki, et al.	
	**	5,896,312	04/20/99	Kozicki, et al.	
JMJ	**	5,914,893	06/22/99	Kozicki, et al.	

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JMT	**	6,084,796	07/04/00	Kozicki, et al.	
	**	2002/0000666	01/03/02	Kozicki	
	**	6,388,324	05/14/02	Kozicki	
	**	6,418,049	07/09/02	Kozicki, et al.	
	**	6,469,364	10/22/02	Kozicki	
	**	6,487,106	11/26/02	Kozicki	
	**	2002/0168820	11/14/02	Kozicki, et al.	
	**	2002/0190350	12/19/02	Kozicki, et al.	
	**	2003/0035314	02/20/03	Kozicki	
	**	2003/0035315	02/20/03	Kozicki	
JMT	**	2003/0048519	03/13/03	Kozicki	

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		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)					
JMT	BA**	56126916		10/19981	Akira et al.		
	BB**	97/48032		12/18/97	WO		
	BC**	99/28914		06/10/99	WO		
	BD**	00/48196		08/17/00	WO		
	BE**	02/21542 A1		03/14/02	WO		
JMT	BF**	02/082452 A2		10/17/02	WO		

Examiner Signature	T. M. Thomas	Date Considered	00-20-05
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		Filing Date	August 29, 2002
		First Named Inventor	Moore, John T.
		Group Art Unit	2818- 2822
		Examiner Name	Nhu, D. T. M. Thomas
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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
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JMJ	CA**	Abdel-All, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge ₅ As ₃₈ Te ₅₇ chalcogenide glass, Vacuum 59 (2000) 845-853.	
	CB**	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189.	
	CC**	Adler, D.; Henisch, H.K.; Mott, S.N., The mechanism of threshold switching in amorphous alloys, Rev. Mod. Phys. 50 (1978) 209-220.	
	CD**	Afifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se ₇₅ Ge ₂₅ -xSbx, Appl. Phys. A 55 (1992) 167-169.	
	CE**	Afifi, M.A.; Labib, H.H.; Fouad, S.S.; El-Shazly, A.A., Electrical & thermal conductivity of the amorphous semiconductor GexSe _{1-x} , Egypt, J. Phys. 17 (1986) 335-342.	
	CF**	Alekperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag ₂ Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.	
	CG**	Aleksiejunas, A.; Cesnys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19 (1973) K169-K171.	
	CH**	Angell, C.A., Mobile ions in amorphous solids, Annu. Rev. Phys. Chem. 43 (1992) 693-717.	
	CI**	Aniya, M., Average electronegativity, medium-range-order, and ionic conductivity in superionic glasses, Solid state Ionics 136-137 (2000) 1085-1089.	
	CJ**	Asahara, Y.; Izumitani, T., Voltage controlled switching in Cu-As-Se compositions, J. Non-Cryst. Solids 11 (1972) 97-104.	
	CK**	Asokan, S.; Prasad, M.V.N.; Parthasarathy, G.; Gopal, E.S.R., Mechanical and chemical thresholds in IV-VI chalcogenide glasses, Phys. Rev. Lett. 62 (1989) 808-810	
	CL**	Axon Technologies Corporation, TECHNOLOGY DESCRIPTION: Programmable Metalization Cell(PMC), pp. 1-6 (Pre-May 2000).	
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		Examiner Name	Nhu, B. T.M. Thomas		
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			First Named Inventor	Moore, John T.
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			Attorney Docket Number	M4065.0989/P989
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